

1N2620, A, B (SILICON)
 thru
1N2624, A, B

Temperature-compensated zener reference diodes utilizing an oxide-passivated junction for long-term voltage stability. Construction consists of welded hermetically sealed metal and glass case.



CASE 52
 (DO-13)



MAXIMUM RATINGS

- Junction Temperature: -55 to +175°C
- Storage Temperature: -65 to +175°C
- DC Power Dissipation: 750 mW @ T_A = 25°C

MECHANICAL CHARACTERISTICS

- CASE: Hermetically sealed, welded metal and glass
- DIMENSIONS: See outline drawing.
- FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
- POLARITY: Cathode to case
- WEIGHT: 1.5 Grams (approx)
- MOUNTING POSITION: Any

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

JEDEC Type No.	Maximum Voltage Change ΔV _Z (Volts) (Note 1)	Ambient Test Temperature °C ±1°C	Temperature Coefficient %/°C (Note 1)	Maximum Dynamic Impedance Z _{ZT} (Ohms) (Note 2)
V _Z = 9.3 V ±5.0%* @ I _{ZT} = 10 mA				
1N2620	0.070	0, +25, +75	0.01	15
1N2621	0.035		0.005	
1N2622	0.014		0.002	
1N2623	0.007		0.001	
1N2624	0.003		0.0005	
1N2620A	0.144	-55, 0, +25, +75, +100	0.01	15
1N2621A	0.072		0.005	
1N2622A	0.029		0.002	
1N2623A	0.014		0.001	
1N2624A	0.007		0.0005	
1N2620B	0.191	-55, 0, +25, +75, +100, +150	0.01	15
1N2621B	0.095		0.005	
1N2622B	0.038		0.002	
1N2623B	0.019		0.001	
1N2624B	0.010		0.0005	

*Tighter-tolerance units available on special request.
 CAPACITANCE (C) = 75 to 200 pF @ 90% of V_Z
 FORWARD BREAKDOWN VOLTAGE (V_F) = 100 to 800 V

